UNR51AVG

Silicon PNP epitaxial planar type

For digital circuits

■ Features

- Costs can be reduced through downsizing of the equipment and reduction of the number of parts.
- SMini type package allowing easy automatic insertion through tape packing

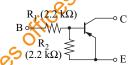
■ Package Code

- SMini3-F2
- Pin Name
 - 1: Base
 - 2: Emitter
 - 3: Collector

■ Absolute Maximum Ratings $T_a = 25$ °C

Parameter	Symbol	Rating	Unit	
Collector-base voltage (Emitter open)	V _{CBO}	-50	V	
Collector-emitter voltage (Base open)	V _{CEO}	-50	V	
Collector current	I_{C}	-80	mA	
Total power dissipation	P _T	150	mW	
Junction temperature	T _j	150	5°C 3	
Storage temperature	T _{stg}	-55 to +150	CO.	

Marking Symbol: EP

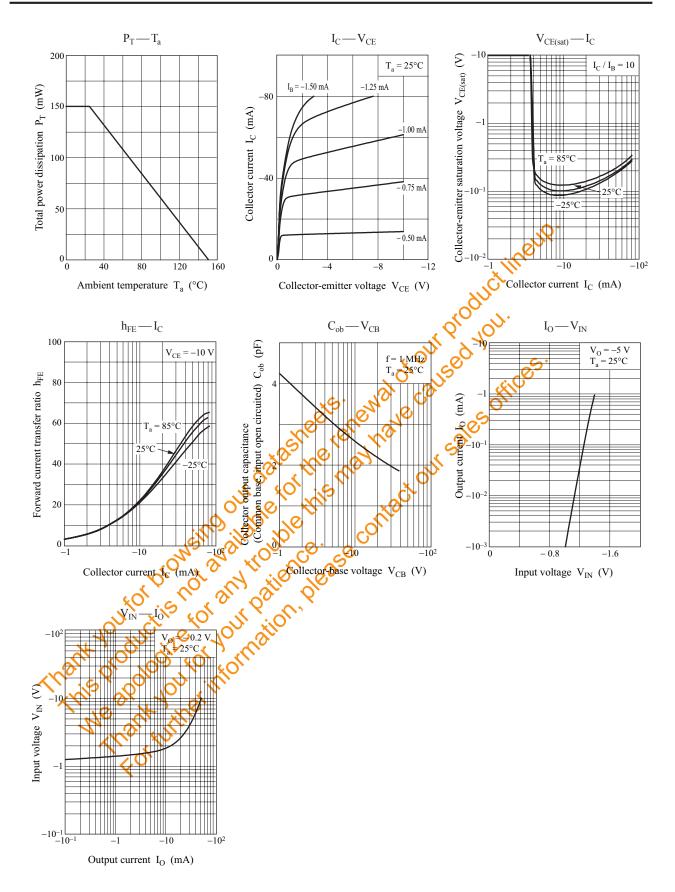


■ Electrical Characteristics $T_a = 2$

Collector-base voltage (Emitter open)	V _{CBO}	-50 V		•					
Collector-emitter voltage (Base open)	V _{CEO}	-50 V	tornal Con	nootion					
Collector current	I _C	-80 mA	Contancon	iriection					
Total power dissipation	P _T	150 mW	R	(2.2 kΩ)	, C				
Junction temperature	T _j	150 S°C NO	Во	R ₂					
Storage temperature	T _{stg} -	-55 to +150	(2.2	$(2 k\Omega)$	• E				
Collector-base voltage (Emitter open) V_{CBO} -50 V V_{CEO} V_{CEO									
Parameter	Symbol	Conditions	Min	Тур	Max	Unit			
Collector-base voltage (Emitter open)	VcBO	$I_{\mathcal{F}} - 10 \text{ pA}, I_{\mathcal{E}} = 0$	-50			V			
Collector-emitter voltage (Base open)	O V _{CEO}	$I_C = -2 \text{mA}, I_B = 0$	-50			V			
Collector-base cutoff current (Emitter oper	i) I _{GBO}	$\nabla_{\rm OB} = -50 \text{ V}, I_{\rm E} = 0$			-0.1	μΑ			
Collector-emitter cutoff current (Base ope	n) I _{CEO}	$V_{CE} = -50 \text{ V}, I_{B} = 0$			- 0.5	μΑ			
Emitter-base cutoff current (Collector oper	i) debo	$V_{EB} = -6 \text{ V}, I_C = 0$			-2.0	mA			
Forward current transfer ratio	h _{FE}	$V_{CE} = -10 \text{ V}, I_{C} = -5 \text{ mA}$	6		20				
Collector-emitter saturation voltage	V _{CE(sat)}	$I_C = -10 \text{ mA}, I_B = -1.5 \text{ mA}$			- 0.25	V			
Output voltage high-level	V _{OH}	$V_{CC} = -5 \text{ V}, V_B = -0.5 \text{ V}, R_L = 1 \text{ k}\Omega$	-4.9			V			
Output voltage low-level	V _{OL}	$V_{CC} = -5 \text{ V}, V_B = -2.5 \text{ V}, R_L = 1 \text{ k}\Omega$			- 0.2	V			
Input resistance	R_1		-30%	2.2	+30%	kΩ			
Resistance ratio	R_1/R_2			1.0		_			
Transition frequency	f_T	$V_{CB} = -10 \text{ V}, I_E = 1 \text{ mA}, f = 200 \text{ MHz}$		80		MHz			

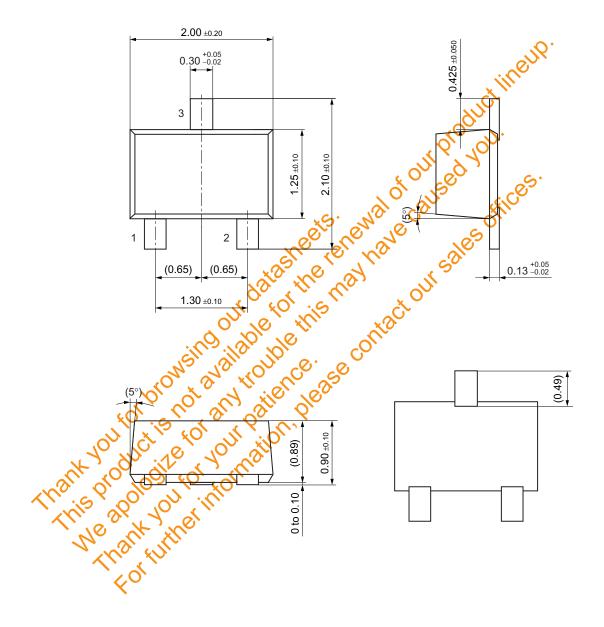
Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

UNR51AVG Panasonic



2 SJH00280AED

SMini3-F2 Unit: mm



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